Crystalline electric field in UFe₄P₁₂

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Recently, Matsuda et al. succeeded in growing single crystals of some uranium-based skutterudite compounds [1]. Among them, UFe₄P₁₂ is known as a small-gap semiconductor and to show the ferromagnetic order below $T_{\rm C}=3.15$ K [2]. We have measured the specific heat, magnetic susceptibility and high-field magnetization in the single crystalline sample of UFe₄P₁₂ in order to clarify the crystalline electric field for a comparative study of U- and Pr-based skutterudite compounds. Figure 1 shows the high-field magnetization at 1.3 K for $H \parallel [100]$. The magnetization shows a ferromagnetic behavior at low fields and saturates above 20 T with a saturation moment of about 1.3 $\mu_{\rm B}/{\rm U}$. The inverse susceptibility for $H \parallel [100]$ follows the Curie-Weiss law in the temperature above 300 K with the effective moment $\mu_{\rm eff} \sim 3~\mu_{\rm B}/{\rm U}$ and the paramagnetic Curie-Weiss temperature $\Theta_{\rm p}=$ -98 K, as shown in the inset of Fig. 1. We analyzed these data by the crystalline electric field model, assuming a 5f² electron configuration for U ions.

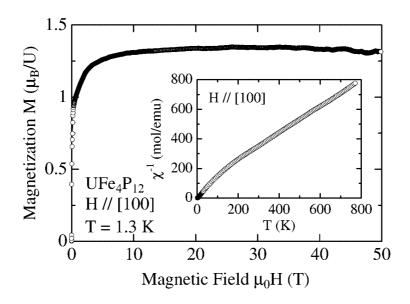


Figure 1: High-field magnetization curve at 1.3 K for H \parallel [100]. The inset shows the temperature dependence of the inverse susceptibility for H \parallel [100].

[1] T. D. Matsuda et al., PS26 in this poster session.

[2] H. Nakotte, N. R. Dilley, M. S. Torikachvili, H. N. Bordallo, M. B. Maple, S. Chang, A. Christianson, A. J. Schultz, C. F. Majkrzak, G. Shirane, Physica B **259-261** (1999) 280.